

SEMITOP[®] 3

3-phase bridge rectifier + brake chopper

SK 95 DGL 126

Features

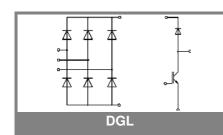
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded alumium oxide ceramic (DCB)
- Trench IGBT technology
- CAL Technology FWD

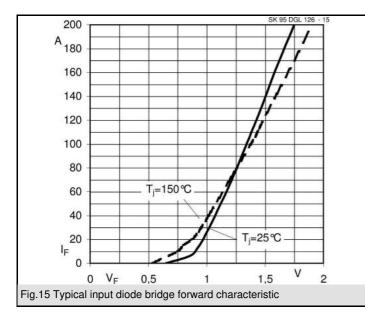
Typical Applications*

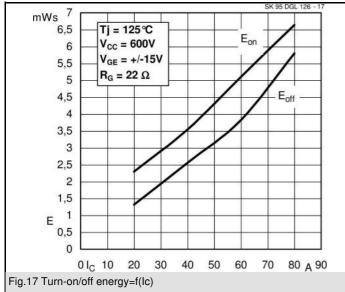
Rectifier

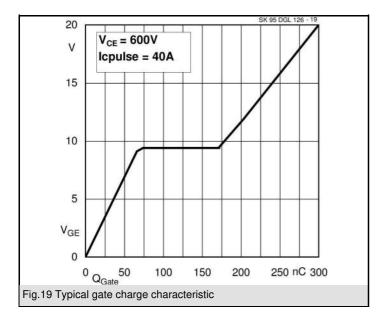
| Symbol | Conditions | Values | Units |
|-------------------------------------|--|-------------|-------|
| IGBT - Ch | opper | | |
| V _{CES} | | 1200 | V |
| I _C | T _s = 25 (80) °C | 40 (32) | А |
| I _{CRM} | I_{CRM} = 2 x I_{Cnom} , t_p = 1 ms | 70 | А |
| V _{GES} | | ±20 | V |
| Т _ј | | -40 +150 | °C |
| Diode - C | hopper | · | |
| I _F | T _s = 25 (80) °C | 45 (35) | А |
| I _{FRM} | $I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$ | 100 | А |
| Т _ј | | -40 +150 | °C |
| Rectifier | | · · · | · |
| V _{RRM} | | 1600 | V |
| I _D | T _s = 80 °C | 96 | А |
| I _{FSM} / I _{TSM} | t _p = 10 ms , sin 180 ° ,T _i = 25 °C | 700 | А |
| I ² t | t _p = 10 ms , sin 180 ° ,T _j = 25 °C | 2450 | A²s |
| T _j | | -40 +150 | °C |
| T _{sol} | Terminals, 10s | 260 | °C |
| T _{stg} | | -40 +125 | °C |
| V _{isol} | AC, 1 min. / 1s | 2500 / 3000 | V |

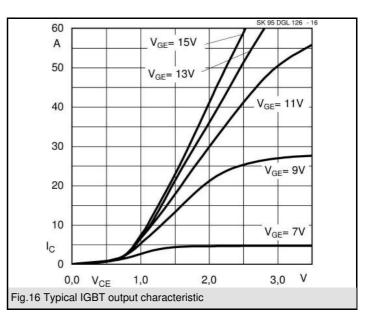
| Characteristics | | T _s = 25°C | T_s = 25°C, unless otherwise specified | | | |
|----------------------------------|---|-----------------------|--|-------------|------|--|
| Symbol | Conditions | min. | typ. | max. | Unit | |
| IGBT - C | hopper | | | | | |
| V _{CEsat} | I _C = 35 A, T _i = 25 (125) °C | | 1,7 (2) | 2,1 | V | |
| V _{GE(th)} | $V_{GE} = V_{CE}$, $I_C = 1,5 \text{ mA}$ | 5 | 5,8 | 6,5 | V | |
| V _{CE(TO)} | T _i = 25 °C (125) °C | | 1 (0,9) | 1,2 | V | |
| r _T | T _j = 25 °C (125) °C | | 20 (31) | 26 | mΩ | |
| C _{ies} | V _{CE} = 25 V _{GE} = 0 V, f = 1 MHz | | 2,4 | | nF | |
| C _{oes} | $V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$ | | 0,5 | | nF | |
| C _{res} | $V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$ | | 0,4 | | nF | |
| R _{th(j-s)} | per IGBT | | | 1,05 | K/W | |
| t _{d(on)} | under following conditions | | 85 | | ns | |
| t _r | V_{CC} = 600 V, V_{GE} = ± 15 V | | 30 | | ns | |
| t _{d(off)} | I _C = 30 A, T _j = 125 °C | | 430 | | ns | |
| t _f | $R_{Gon} = R_{Goff} = 22 \Omega$ | | 90 | | ns | |
| E _{on} | inductive load | | 4,6 | | mJ | |
| E _{off} | | | 4,3 | | mJ | |
| Diode - C | Chopper | | | | | |
| V _F = V _{EC} | I _F = 45 A, T _i = 25(150) °C | | 1,5 (1,5) | 1,77 (1,77) | V | |
| V _(TO) | $T_{i} = C (125) C$ | | (0,92) | | V | |
| r _T | $T_{i} = C (125) C$ | | (13,4) | | mΩ | |
| R _{th(j-s)} | per diode | | | 1,2 | K/W | |
| I _{RRM} | under following conditions | | 30 | | Α | |
| Q _{rr} | I _F = 50 A, V _R = 600 V | | 10 | | μC | |
| Err | V _{GE} = 0 V, T _i = 125 °C | | | | mJ | |
| | di _{F/dt} = 500 A/µs | | | | | |
| Diode re | ctifier | • | | | | |
| V _F | I _F = 35 A, T _i = 25(125) °C | | - | 1,2 | V | |
| V _(TO) | T _i = 150 °C | | | 0,8 | V | |
| r _T | T _i = 150 °C | | | 11 | mΩ | |
| R _{th(j-s)} | per diode | | | 1,2 | K/W | |
| | tur sensor | | | | | |
| R _{ts} | %, T _r = () °C | | () | | Ω | |
| Mechani | | I | | | 1 | |
| w | | | 30 | | g | |
| | Mounting torque | 1 | | | 1 - | |

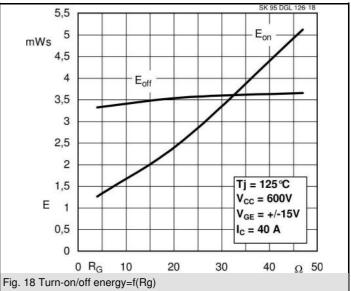


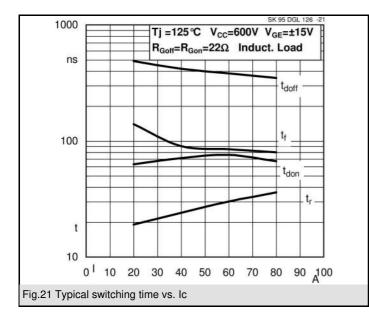


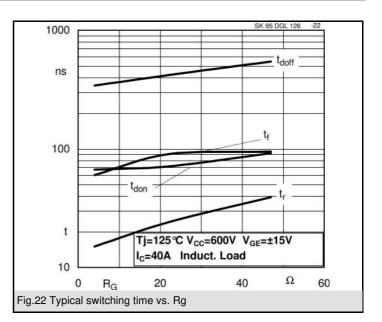


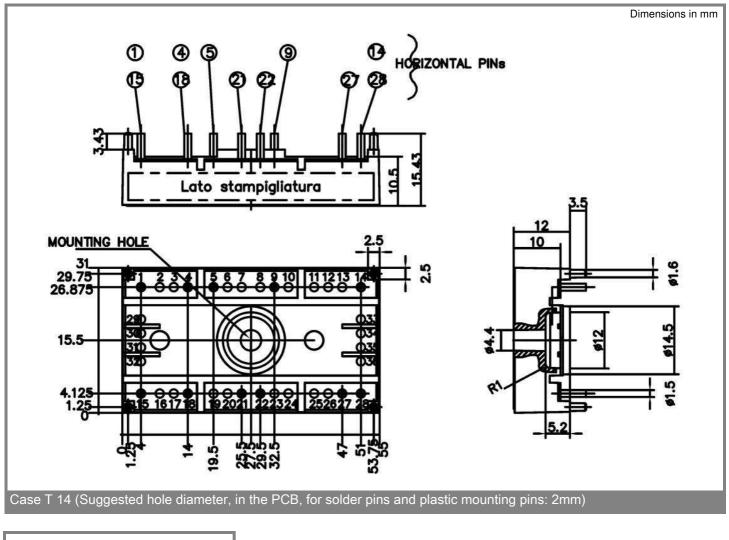


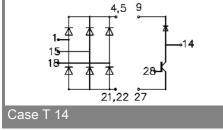












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.